

Workshop on Band gap reference design

Summary:

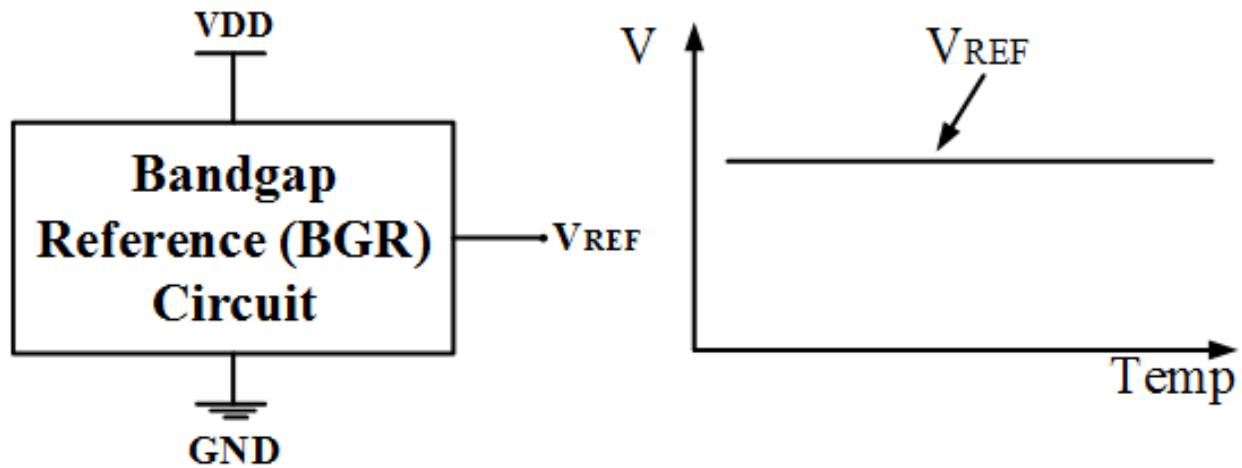
2-day hands on lab-based workshop on Analog Bandgap IP design using SKY 130, an opensource 130nm PDK made available by collaboration between Google and Sky Water Technology Foundry. Workshop covers BGR are design from scratch to post layout simulation. On Day1 the course provides profound background on the theory of BGR, BGR's description, application, implementation and need. Day 2 provide hands on experience in BGR design using ngspice, magic and netgen. After the course one will be able to understand concept of BGR, how CTAT and PTAT blocks are designed to get remove temperature dependency and implement solution to generate constant voltage as per the required specs.

INDEX

- Day 1: BGR Theory and Lab setup
 - Part 1: Introduction to BGR
 - Part 2: Tools and PDK setup
 - Part 3: Design spec and data analysis
 - Part 4: CTAT voltage generation circuit
 - Part 5: PTAT voltage generation circuit
 - Part 6: Biased current mirror circuit
 - Part 7: Reference voltage branch circuit
 - Part 8: Start-up circuit
 - Part 9: complete BGR circuit
 - Part 10: Layout of components
 - Part 11: Top level extraction and LVS
- Conclusion and Opinion
- References

PART1: Introduction to BGR

BGR is a temperature independent voltage reference widely used in integrated circuits. It produces a constant voltage regardless of power supply and variation in temperature.



Why BGR

There is a need for a device to provide a constant voltage independent of variation in power supply and temperature. A battery drops voltage over time. A typical power supply is noisy or has ripples and IC using Zener cannot be used due to high thermal noise and unavailability of lower voltage Zener's.

Solution

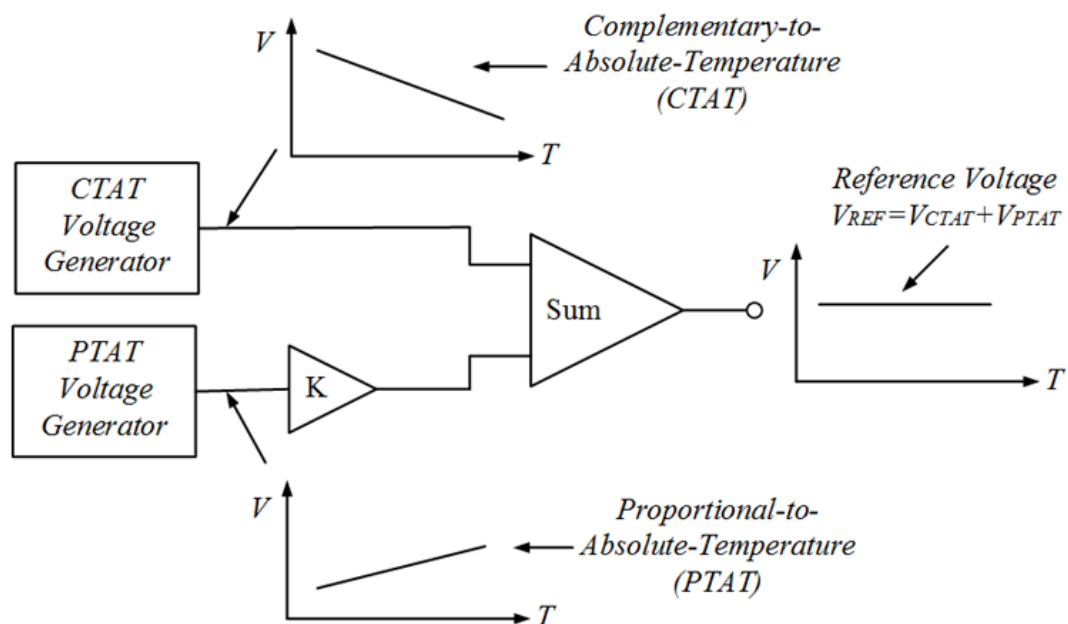
- A Bandgap reference which can be integrated in bulk CMOS, Bi-CMOS or Bipolar technologies without the use of external components.

Applications of BGR

- Low dropout regulators (LDO)
- DC-to-DC buck converters
- Analog-to-Digital Converter (ADC)
- Digital-to-Analog Converter (DAC)

BGR Principle

All devices inherently either have positive temperature coefficient or negative temperature coefficient. The operation principle of BGR circuits is to sum a voltage with negative temperature coefficient with another one with positive temperature coefficient. The two-temperature coefficient are designed so as to cancel each other out so that overall resultant is temperature independent. Generally, constant current supplied into semiconductor diode behave as CTAT i.e., complement to absolute temp. So, we need to design a PTAT i.e., proportional to absolute temp ($V_T = KT/Q$) which can cancel out the CTAT nature i.e., with rise in temp.



Types of BGR

Based on architecture there are two types

1. Self-biased current mirror: Stable and simple design but has low PSRR and needs start-up circuit.
2. Using operational amplifier

Based on application BGR is characterised into 4 types

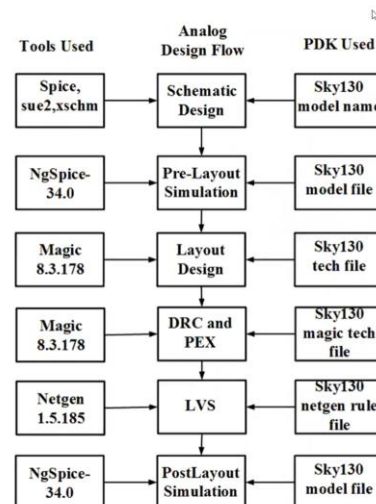
1. Low-voltage BGR
2. Low-power BGR
3. High-PSRR and low noise BGR
4. Curvature compensated BGR

PART 2: Tools and PDK setup

- Tools used:
 - Ngspice: It is used for the transistor level circuit simulation and design.
 - Magic: It is used for layout design and parasitic extraction

Both Ngspice and Magic are open-source tools which need to be downloaded and installed to the work environment.

- Development Flow and tool used:

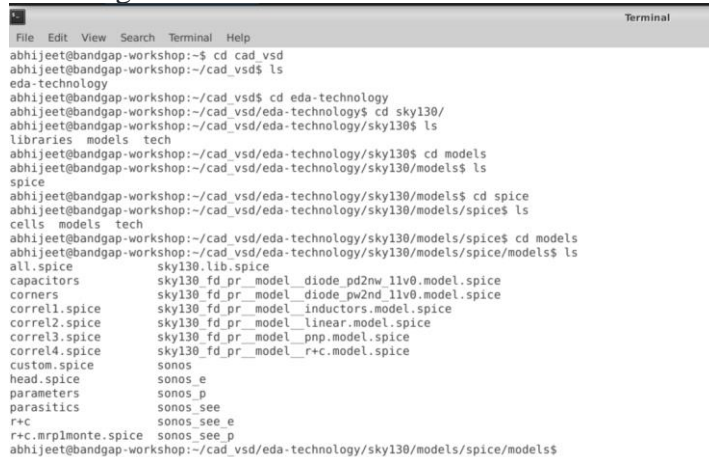


- Next, we need we have to clone the google skywater pdk. On the terminal type `git clone` https://github.com/google/skywater-pdk-libs-sky130_fd_pr.git or Git clone <https://github.com/silicon-vlsi-org/eda-technology>

```
Terminal
File Edit View Search Terminal Help

abhijeet@bandgap-workshop:~$ mkdir cad_vsd
abhijeet@bandgap-workshop:~$ cd cad_vsd
abhijeet@bandgap-workshop:~/cad_vsd$ git clone https://github.com/silicon-vlsi-org/eda-technology
Cloning into 'eda-technology'...
remote: Enumerating objects: 4176, done.
remote: Counting objects: 100% (4176/4176), done.
remote: Compressing objects: 100% (880/880), done.
remote: Total 4176 (delta 3292), reused 4157 (delta 3281), pack-reused 0
Receiving objects: 100% (4176/4176), 118.36 MiB | 17.47 MiB/s, done.
Resolving deltas: 100% (3292/3292), done.
Checking out files: 100% (3913/3913), done.
abhijeet@bandgap-workshop:~/cad_vsd$
```

- Once all tools and pdk are set up ensure all tools are working properly.
 - Checking all model file.

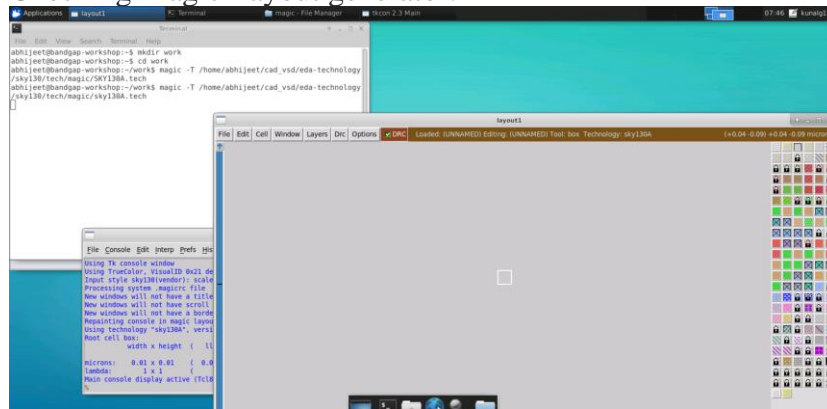


```

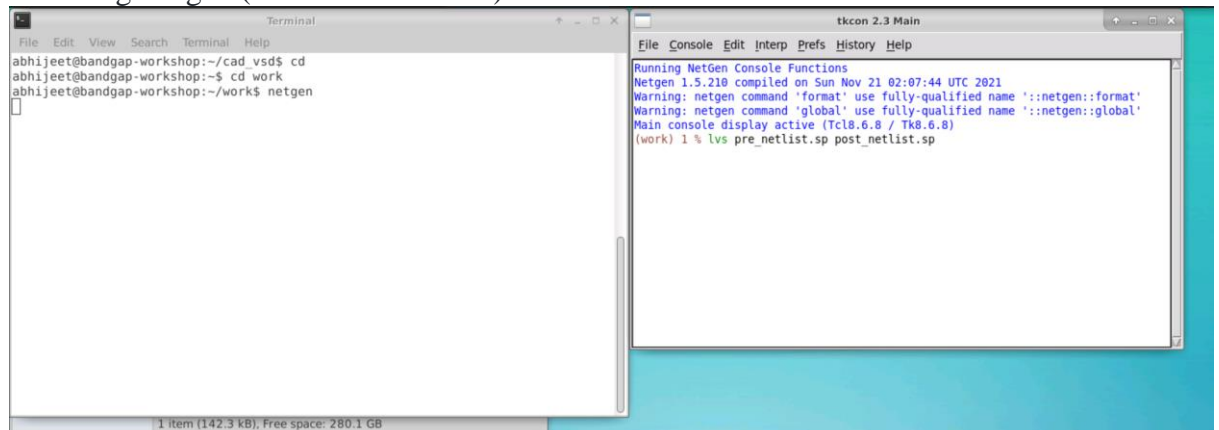
abhiyeet@bandgap-workshop:~$ cd cad_vsd
abhiyeet@bandgap-workshop:~/cad_vsd$ ls
eda-technology
abhiyeet@bandgap-workshop:~/cad_vsd$ cd eda-technology
abhiyeet@bandgap-workshop:~/cad_vsd/eda-technology$ cd skyl30/
abhiyeet@bandgap-workshop:~/cad_vsd/eda-technology/skyl30$ ls
libraries models tech
abhiyeet@bandgap-workshop:~/cad_vsd/eda-technology/skyl30$ cd models
abhiyeet@bandgap-workshop:~/cad_vsd/eda-technology/skyl30/models$ ls
spice
abhiyeet@bandgap-workshop:~/cad_vsd/eda-technology/skyl30/models$ cd spice
abhiyeet@bandgap-workshop:~/cad_vsd/eda-technology/skyl30/models/spice$ ls
cells models tech
abhiyeet@bandgap-workshop:~/cad_vsd/eda-technology/skyl30/models/spice$ cd models
abhiyeet@bandgap-workshop:~/cad_vsd/eda-technology/skyl30/models/spice/models$ ls
all.spice          skyl30.lib.spice
capacitors         skyl30_fd_pr_model_diode_pd2nw_1lv0.model.spice
corners            skyl30_fd_pr_model_diode_pw2nd_1lv0.model.spice
correl1.spice      skyl30_fd_pr_model_inductors.model.spice
correl2.spice      skyl30_fd_pr_model_linear.model.spice
correl3.spice      skyl30_fd_pr_model_pnp.model.spice
correl4.spice      skyl30_fd_pr_model_rc.model.spice
custom.spice       sonos
head.spice         sonos_e
parameters         sonos_p
parasitics         sonos_see_e
r+c               sonos_see_e
r+c.mrp1monte.spice sonos_see_p
abhiyeet@bandgap-workshop:~/cad_vsd/eda-technology/skyl30/models/spice/models$

```

- Checking Magic Layout generator.



- Checking Netgen (used to check LVS)



Part 3: Design spec and data analysis

First thing before getting into design is to define the specifications. The device needs to be operated with in the specifications. For BGR below mentioned are the general specifications.

- Supply voltage = 1.8V
- Temperature: -40 to 125 Deg Cent.
- Power Consumption < 60uW
- Off current < 2uA
- Start-up time < 2us
- Tempco. Of Vref < 50 ppm

It can be observed that for BGR the power consumption, temperature coefficient and start up time need to be low.

Well defined specification helps us in choosing the Mosfets, resistors and transistors need to design BGR. For the current design following devises will be used.

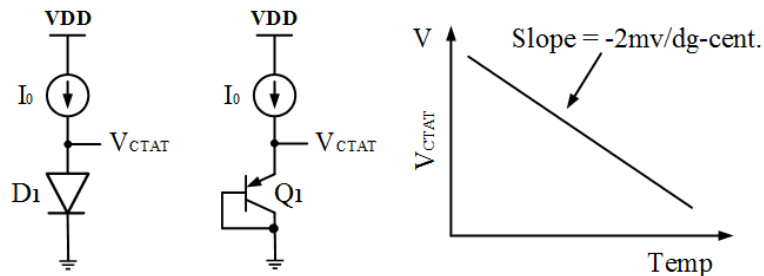
MOSFET		NFET (MOSFET)	PFET (MOSFET)
	Type	LVT	LVT
	Voltage	1.8V	1.8V
	Thres. Voltage	~ 0.4V	~-0.6V
	Model Name	Sky130_fd_pr__nfet_01v8_lvt	Sky130_fd_pr__pfet_01v8_lvt

BJT		PNP (BJT)
	Current Rating	1uA-10uA/um ²
	Beta	~12
	Emitter Area	11.56 um ²
	Model Name	Sky130_fd_pr__pnp_05v5_W3p40l3p40

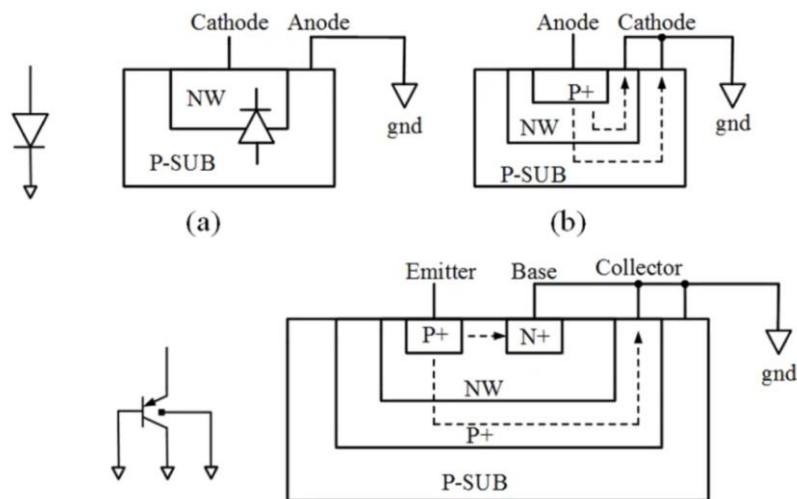
RESISTOR		RPOLYH (RESISTOR)
	Sheet Resistance	~350 Ohm
	Tempco.	2.5 Ohm/Deg Cent.
	Bin width	0.35u, 0.69u, 1.41u, 2.85u and 5.73u
	Model Name	Sky130_fd_pr__res_high_po

Part 4: CTAT voltage generation circuit

If we consider constant current is flowing through a forward biased diode, then with increase in temp. we can observe that the voltage across the diode is decreasing. Generally, it is found that the slope of the $V \sim \text{Temp}$ is $-2\text{mV/deg Centigrade}$.



While manufacturing a diode it forms a parasitic PNP transistor which leaks large current into substrate if there is a small base current. This may affect other devices present in the same substrate. In order to avoid it a diode connected transistor is used to generate CTAT. P+ diffusion is done in P-SUB and PN junction is formed in the P+ region. Now when there is base current in N+ region the large current flows from emitter to collector (P+) and doesn't leak into P-sub.



The Diode current is defined as

$$I_D = I_S e^{\frac{V_D}{V_t}} \dots \dots \dots (1)$$

Which can be written as

$$V_D = V_t \ln\left(\frac{I_0}{I_S}\right) \dots \dots \dots (2)$$

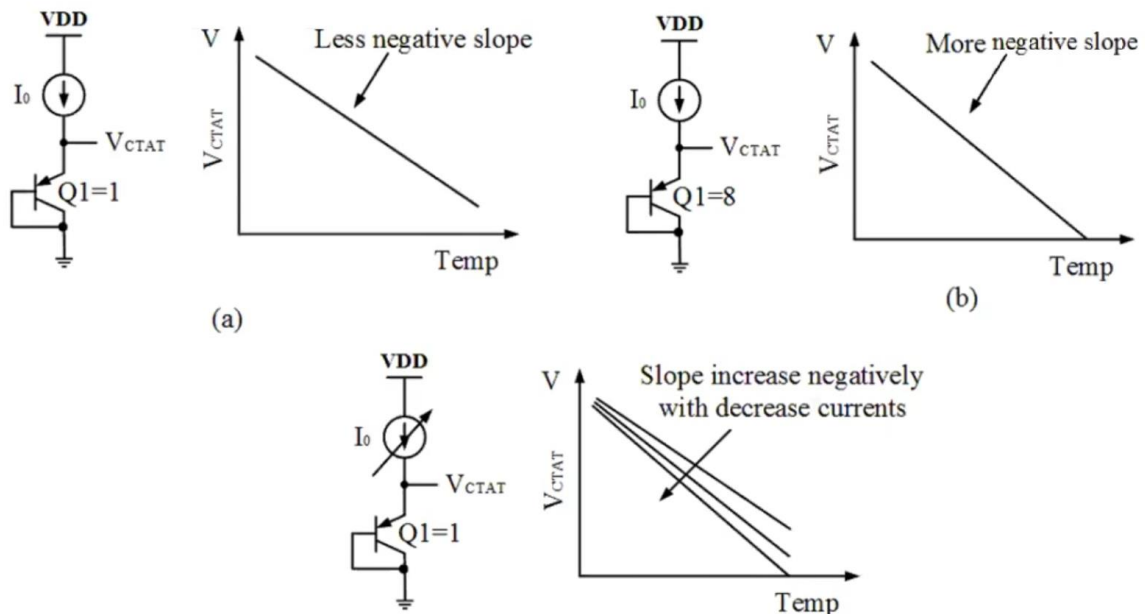
Variation of V_d wrt to temperature can be obtained by differentiating the equation 2 and it can be shown that voltage V_{ctat} can be expressed as below

$$\frac{dV}{dT} = \frac{V_D - (4 + m)V_t - \frac{E_g}{q}}{T} \dots\dots\dots(3)$$

By replacing the standard values for the above variable, it can be seen that temperature coefficient of diode connected mosfet is closed to 1.88mv/degK

$$\frac{dV}{dT} = \frac{0.7 - (4 - 1.5) * 0.026 - 1.2}{300} = -1.88mv / \text{deg } k$$

The negative slope of CTAT circuit can be controlled by varying the current supplied to the transistor or by having multiple transistors connected in parallel.



Current mirror is highly dependent on VDD hence self-biased current mirror is used.

Implantation of CTAT:

CTAT is implemented by connecting a constant current source to a diode connected mosfet.

Ensure to include the sky130.lib.spice TT (TT for typical- typical process) and

Sky130_fd_pr__model__pnp.model.spice


```
Applications  ptat_circuit.sp (~/.wor...  Terminal  prelayout - File Manager  work - File Manager  models - File Manager  abhijeet - File Manager
```

```
File Edit View Search Terminal Help

*** ctat voltage generation ***
.lib "/home/abhijeet/cad_vsd/eda-technology/sky130/models/spice/models/sky130.lib.spice tt"
.include "/home/abhijeet/cad_vsd/eda-technology/sky130/models/spice/models/sky130_fd_pr_model__pnp.model.spice"

.global vdd gnd
.temp=27

*** bjt definition ***
xq1 gnd gnd q1 gnd sky130_fd_pr__pnp_05v5_w3p40l3p40 m=1

*** supply voltage and current
vsup vdd gnd dc 2
isup vdd q1 dc 10u
.dc temp -40 125 5

.control
run
plot v(q1)
.endc
.end
```

```
File Edit View Search Terminal Help

abhijeet@bandgap-workshop:~$
abhijeet@bandgap-workshop:~$
abhijeet@bandgap-workshop:~$ cd work
abhijeet@bandgap-workshop:~/work$ vim ptat_circuit.sp
abhijeet@bandgap-workshop:~/work$ vim ptat_circuit.sp
abhijeet@bandgap-workshop:~/work$
abhijeet@bandgap-workshop:~/work$
abhijeet@bandgap-workshop:~/work$
abhijeet@bandgap-workshop:~/work$ vim ctat_voltage_gen.sp.
abhijeet@bandgap-workshop:~/work$ ngspice ctat_voltage_gen.sp
```

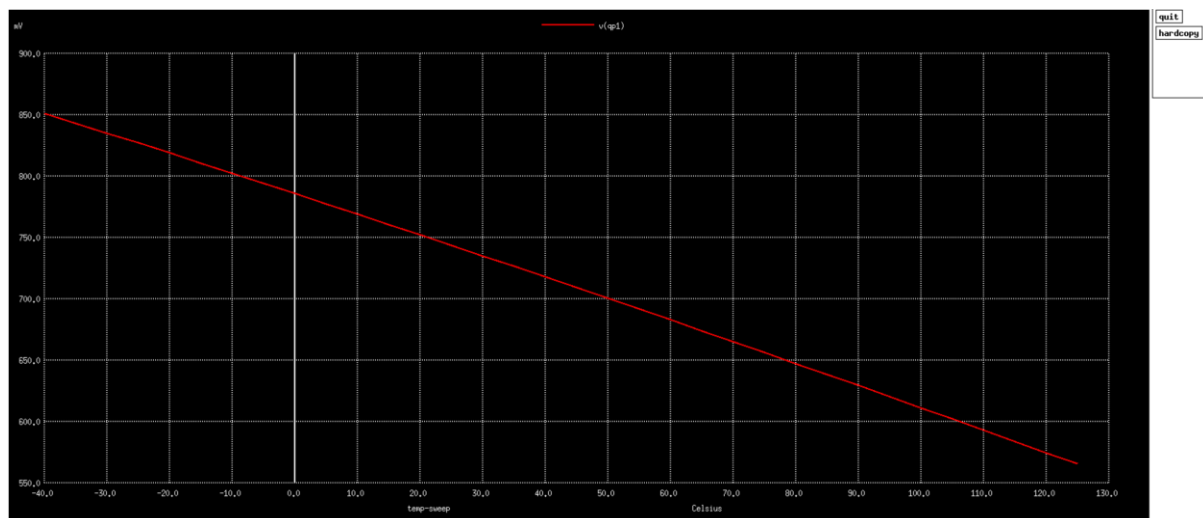
```
Applications  ptat_curcuit.sp (~/.  Terminal  prelayout - File Ma  work - File Manager  models - File Mana  abhijeet - File Man...  work - File Manager  10:04 kunalg123
```

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File Edit View Search Terminal Help
abhijeet@bandgap-workshop:~$
abhijeet@bandgap-workshop:~$
abhijeet@bandgap-workshop:~$ cd work
abhijeet@bandgap-workshop:~/work$ vim ptat_curcuit.sp
abhijeet@bandgap-workshop:~/work$ vim ptat_curcuit.sp
abhijeet@bandgap-workshop:~/work$
abhijeet@bandgap-workshop:~/work$
abhijeet@bandgap-workshop:~/work$
abhijeet@bandgap-workshop:~/work$ vim ctat_voltage_gen.sp
abhijeet@bandgap-workshop:~/work$ ngspice ctat_voltage_gen.sp
*****
** ngspice-27 : Circuit level simulation program
** The U. C. Berkeley CAD Group
** Copyright 1985-1994, Regents of the University of California.
** Please get your ngspice manual from http://ngspice.sourceforge.net/docs.html
** Please file your bug-reports at http://ngspice.sourceforge.net/bugrep.html
** Creation Date: Tue Dec 26 17:10:20 UTC 2017
*****
ctat_voltage_gen.sp: No such file or directory
ngspice 1 ->
```

[illegible]

- Test case1: $I_d=10\mu A$, $M=1$.

Resultant slope=-0.0017074



No. of Data Rows : 34

ngspice 1 ->

$x_0 = -19.8864$, $y_0 = 0.818023$ $x_1 = 78.5227$, $y_1 = 0.65$

$dx = 98.4091$, $dy = -0.168023$

$dy/dx = -0.0017074$ $dx/dy = -585.687$

- Test case2: $I_d=10\mu A$, $M=8$.

Resultant slope=-0.0019138

```
Applications  ptat_circuit.sp (~/.work...  Terminal  prelayout - File Manager  work - File Manager  models - File Manager

Terminal
File Edit View Search Terminal Help
.lib "/home/abhiyeet/cad_vsd/eda-technology/skyl30/models/spice/models/skyl30.lib.spice tt"
.include "/home/abhiyeet/cad_vsd/eda-technology/skyl30/models/spice/models/skyl30_fd_pr__model__pnp.model.spice"

**** ctat voltage generation circuit with multiple bjt ****

.lib "/home/srath22/cad/eda-technology/skyl30/models/spice/models/skyl30.lib.spice tt"
.include "/home/srath22/cad/eda-technology/skyl30/models/spice/models/skyl30_fd_pr__model__pnp.model.spice"

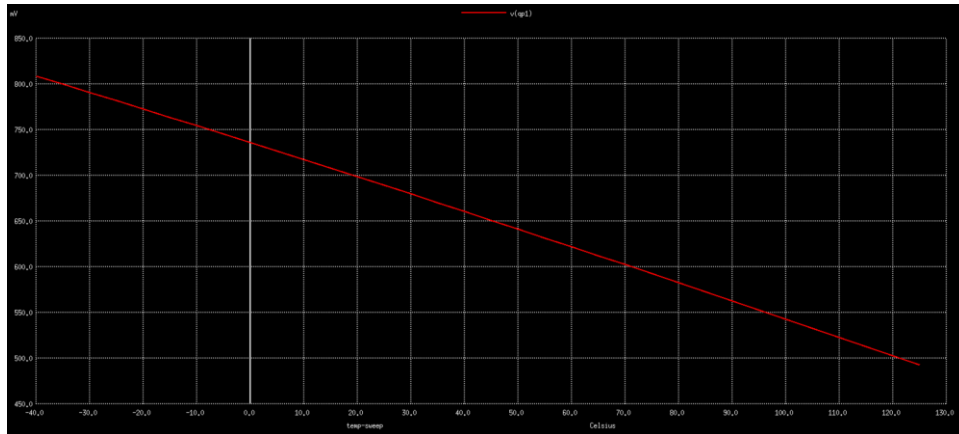
.global vdd gnd
.temp 27

*** bjt definition
xqpl  gnd  gnd  qpl  gnd  skyl30_fd_pr__pnp_05v5_W3p40L3p40  m=8

*** supply voltage and current
vsup  vdd  gnd  dc  2
isup  vdd  qpl  dc  10u
.dc  temp  -40  125  5

*** control statement
.control
run
plot v(qpl)
.endc
.end

abhiyeet@bandgap-workshop:~/work$ vim ctat_voltage_gen_mul_bjt.sp
abhiyeet@bandgap-workshop:~/work$
abhiyeet@bandgap-workshop:~/work$ vim ctat_voltage_gen_mul_bjt.sp
abhiyeet@bandgap-workshop:~/work$ ngspice ctat_voltage_gen_mul_bjt.sp
*****
** ngspice-27 : Circuit level simulation program
** The U. C. Berkeley CAD Group
** Copyright 1985-1994, Regents of the University of California.
** Please get your ngspice manual from http://ngspice.sourceforge.net/docs.html
** Please file your bug-reports at http://ngspice.sourceforge.net/bugrep.html
** Creation Date: Tue Dec 26 17:10:20 UTC 2017
*****
```



No. of Data Rows : 34

ngspice 1 ->

x0 = 0.113636, y0 = 0.733333 x1 = 95.9091, y1 = 0.55

dx = 95.7955, dy = -0.183333

dy/dx = -0.0019138 dx/dy = -522.521



- Test case3: Id=1.25u to 10uA, M=1. Resultant slope=-0.0017166 to -0.00187869

```
abhijeet@bandgap-workshop:~/work$ vim ctat_voltage_gen_var_current.sp
abhijeet@bandgap-workshop:~/work$ ngspice ctat_voltage_gen_var_current.sp
```

** ngspice-27 : Circuit level simulation program

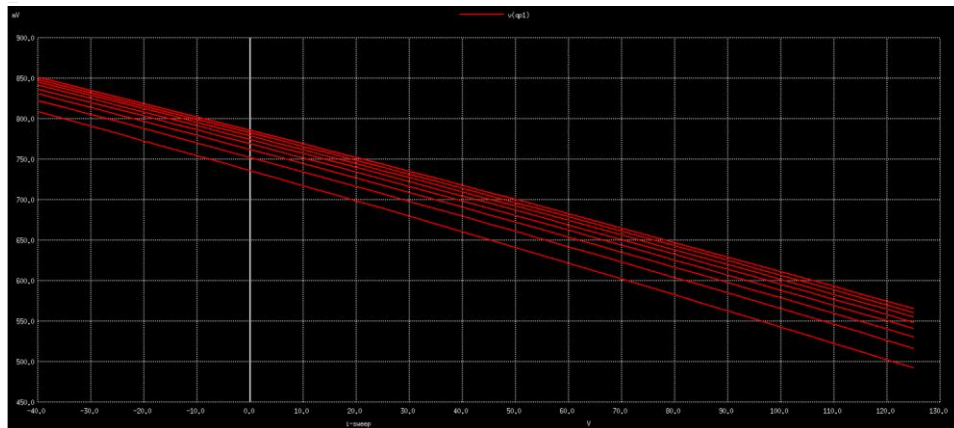
** The U. C. Berkeley CAD Group

** Copyright 1985-1994, Regents of the University of California.

** Please get your ngspice manual from <http://ngspice.sourceforge.net/docs.html>

** Please file your bug-reports at <http://ngspice.sourceforge.net/bugrep.html>

** Creation Date: Tue Dec 26 17:10:20 UTC 2017



No. of Data Rows : 272

ngspice 1 ->

x0 = 126.477, y0 = 0.776119

x0 = -19.8864, y0 = 0.770896 x1 = 70.6818, y1 = 0.600746

dx = 90.5682, dy = -0.170149

dy/dx = -0.00187869 dx/dy = -532.287

x0 = -29.8864, y0 = 0.833582 x1 = 109.659, y1 = 0.59403

dx = 139.545, dy = -0.239552

dy/dx = -0.00171666 dx/dy = -582.526

PART5: PTAT Voltage Generation

From Diode current equation (2) we can find that it has two parts, i.e.

- V_t (Thermal Voltage) which is directly proportional to the temp. (KT/Q)
- I_s (Reverse saturation current) which is directly proportional to the temp. ($A\mu kTn_i^2$), as this I_s term is in denominator so with increase in temp. the $\ln(I_o/I_s)$ decreases which is responsible for CTAT nature of the diode.

$$I_D = I_S e^{\frac{V_D}{V_t}}$$

$$V_D = V_t \ln\left(\frac{I_D}{I_S}\right)$$

$$V_t = \frac{kT}{q}$$

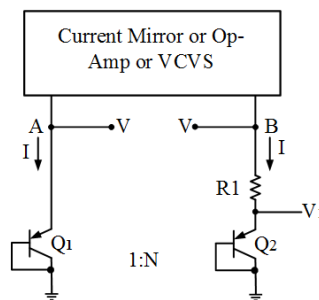
$$I_S = A\mu kTn_i^2$$

$$\mu \propto \mu_0 T^m, m = -3/2$$

$$n_i^2 \propto T^3 e^{\left[\frac{-E_g}{kT}\right]}$$

$$I_S = AT^{(4+m)} e^{\left[\frac{-E_g}{kT}\right]}$$

So, to get a PTAT Voltage generation circuit V_t needs to be separated from I_s .



In the above circuit same amount of current I is flowing in both the branches. So, the node voltage A and B are going to be same V . Now in the B branch if we subtract V_1 from V , we get V_t independent of I_s .

$$V = V_t \ln \frac{I}{I_s} \quad \text{and} \quad V_1 = V_t \ln \frac{I/N}{I_s}$$

$$V - V_1 = V_t \ln(N)$$

$$V_t = \text{PTAT and } \ln(N) = \text{constant}$$

$$V_t = \frac{kT}{q}, \quad \frac{d(V_t)}{dT} = \frac{k}{q} = 85\mu\text{V}/\text{DegCent}.$$

From above we can see that the voltage $V - V_1$ is PTAT in nature, but its slope is very less as compared to the CTAT, so we have to increase the slope.

The figure consists of a schematic diagram on the left and two graphs on the right.

Schematic Diagram: A circuit labeled "Current Mirror or Op-Amp or VCVS" is connected to two transistors, Q_1 and Q_2 , which are in a $1:N$ ratio. Transistor Q_1 has its emitter grounded and its collector connected to node A. Transistor Q_2 has its emitter grounded and its collector connected to node B. A resistor R_1 is connected between node B and the base of Q_2 . The voltage across R_1 is V_1 . The voltage between node A and node B is V . Currents I and I_1 are indicated flowing downwards from nodes A and B, respectively.

Graphs:

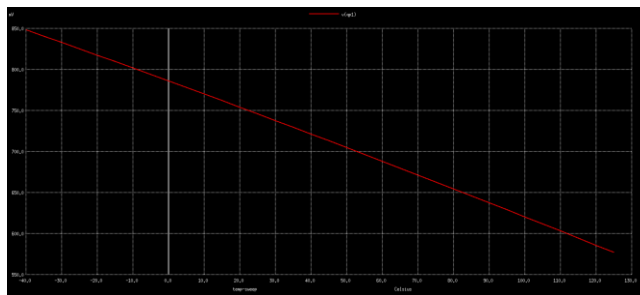
- The top graph plots Voltage versus Temperature (Temp). It shows a straight line with a positive slope labeled $V - V_1$ and a line with a shallower positive slope labeled "PTAT Voltage".
- The bottom graph plots Voltage versus Temperature (Temp). It shows two lines with negative slopes. The upper line is labeled V_1 and the lower line is labeled V .

PTAT is implemented by connecting a constant current source to a diode connected mosfets in node A and B with a resistor R1 connected to node B.

Sky130_fd_pr__model__pnp.model.spice

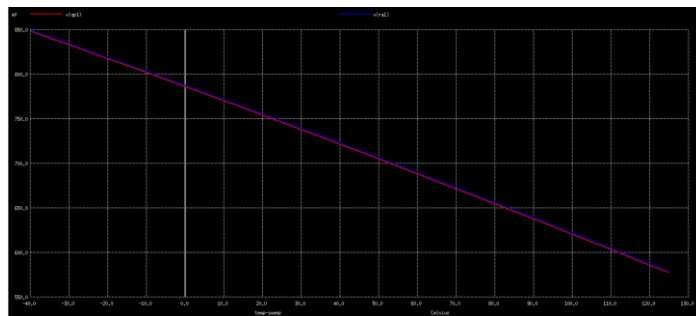
[illegible]

qp1 result is CTAT in nature

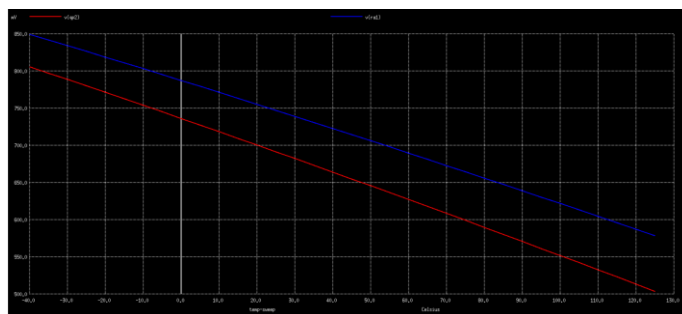


```
No. of Data Rows : 34
ngspice 1 -> plot (v(qp1))
PError: syntax error
ngspice 1 -> plot v(qp1)
ngspice 1 ->
x0 = 130.455, y0 = 0.64703
x0 = -8.86364, y0 = 0.8    x1 = 82.6136, y1 = 0.649505
dx = 91.4773, dy = -0.150495
dy/dx = -0.00164516    dx/dy = -607.842
```

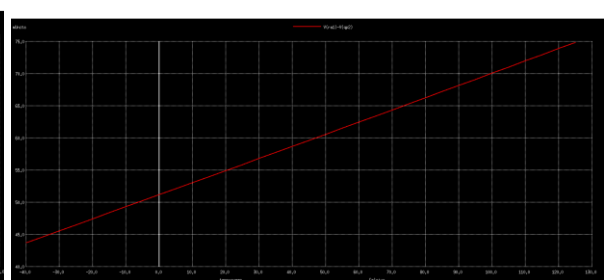
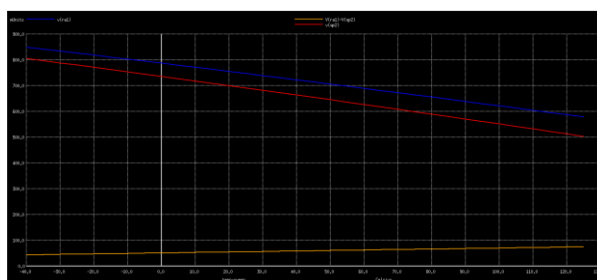
$V(qp1) \approx V(Ra1)$



In below wave form it can be observed that $V(qp2)$ has different slope than $V(Ra1)$



On subtracting $V(Ra1)$ $V(qp2)$ PTAT result is obtained, Resultant slope=0.00190636



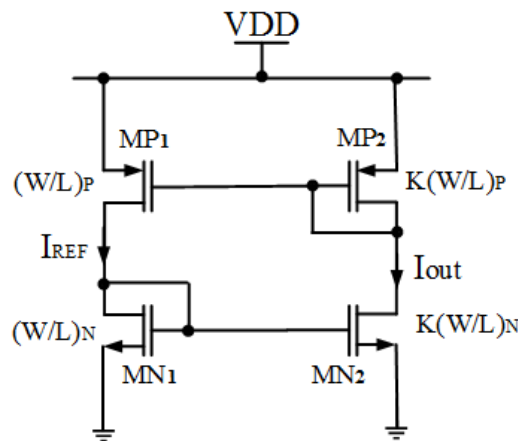
```
ngspice 1 -> plot v(qp2) v(Ra1) V(Ra1)-V(qp2)
ngspice 1 -> plot V(Ra1)-V(qp2)
ngspice 1 ->
x0 = -37.0787, y0 = 0.055407
x0 = -6.17978, y0 = 0.0499419    x1 = 89.8876, y1 = 0.0682558
dx = 96.0674, dy = 0.018314
dy/dx = 0.000190636    dx/dy = 5245.59
```

Part 6: Biased current mirror circuit

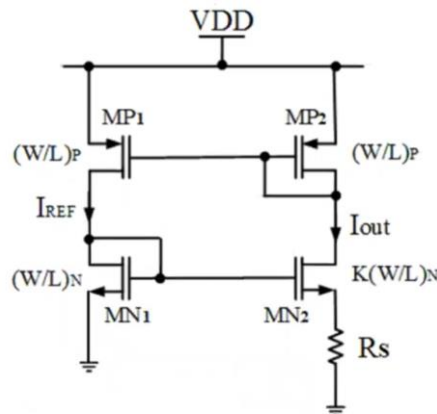
For both CTAT and PTAT design it was observed previously that a constant current source is required in order to obtain the desired slope of voltage wrt to temperature.

In a current mirror I_{ref} sets I_{out} but I_{out} is tied closely with supply voltage. any variation in supply affects I_{ref} and there by affecting the voltage reference. In order to improve PSRR of the system the current mirror should be able to bias itself i.e, I_{ref} is derived from I_{out} .

The Self-biased current mirror is a type of current mirror which requires no external biasing. This current mirrors biases itself to the desired current value without any external current source reference.



In the above circuit MP2 and MP1 copy I_{out} and define I_{ref} (I_{ref} is bootstrapped to I_{out}). The device is governed by $I_{ref} = K \cdot I_{out}$, hence it can support any current.



R_s is used to uniquely define current, loop gain is always less than 1. i.e, the circuit is generally stable and an external circuit is need to drive the device to correct bias point.

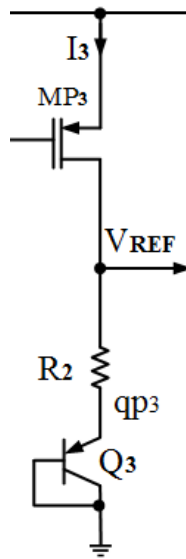
$$I_{out} = \frac{2}{\mu_n C_{ox} (W/L)_N} \cdot \frac{1}{R_s^2} \left(1 - \frac{1}{\sqrt{K}} \right)^2$$

I_{out} is defined by the above equation.

Part 7: Reference voltage branch circuit

CTAT, PTAT and their current source is designed. Next step is to add CTAT and PTAT to generate the required reference voltage.

The reference circuit branch performs the addition of CTAT and PTAT voltages and gives the final reference voltage. MP3 is used as a mirror transistor to keep the current same as current mirror branches, R2 is used to scale PTAT to the same value as CTAT so that they cancel each other out and a BJT as diode in the reference branch.



$$R2 = \alpha * R1$$

$$\frac{dV_{R2}}{dT} + \frac{dV_{Q3}}{dT} = 0$$

$$\frac{d\alpha * V_{R1}}{dT} + \frac{dV_{Q3}}{dT} = 0$$

$$\frac{d(\alpha * V_t \ln N)}{dT} + \frac{dV_{Q3}}{dT} = 0$$

$$(\alpha * \ln N) \frac{dV_t}{dT} + \frac{dV_{Q3}}{dT} = 0$$

$$\frac{dV_{Q3}}{dT} = -1.6 \text{ mV/deg cent.}$$

$$\frac{dV_t}{dT} = 85 \text{ uV/deg cent.}$$

Part 8: Start-up circuit

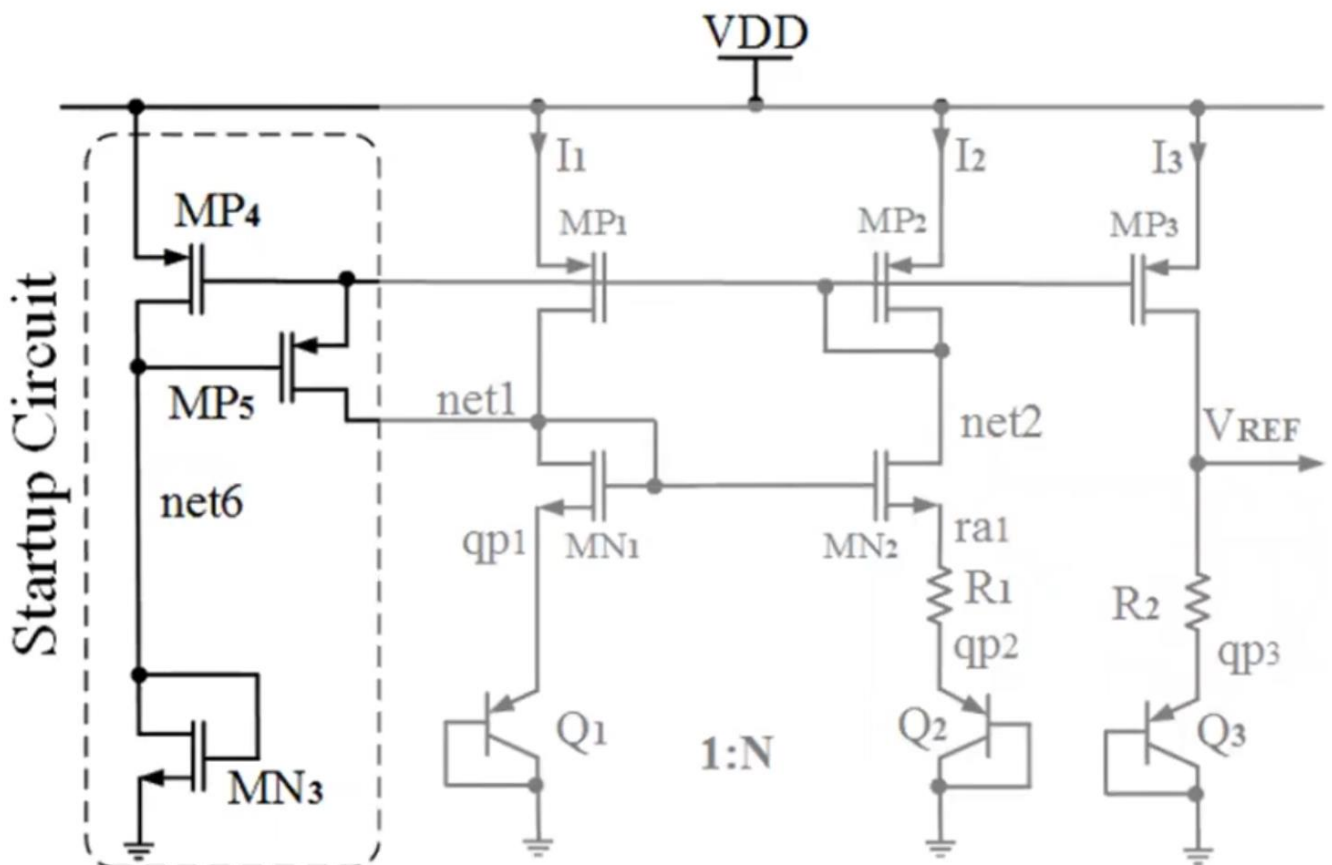
Why Start-up?

In self-biased current mirror circuit if channel length modulation is ignored there is very little dependency on the supply voltage. This leads to existence of a degenerate bias point i.e device is stable at $I_{in}=I_{out}=0A$. Even if the Supply is turned on there is no force to drive the currents and therefore voltage to the required operating point.

A circuit is added to drive the device into the desired operating point and once device operation reaches steady state the circuit should no longer interfere.

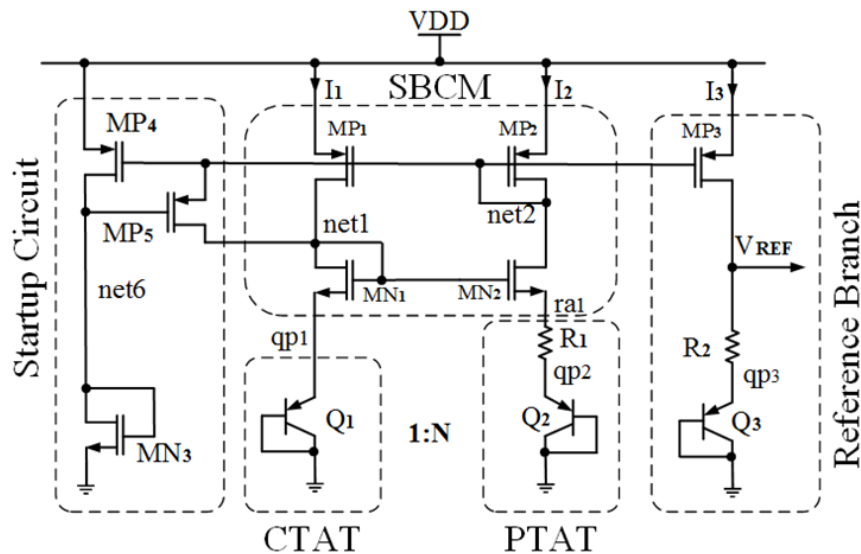
Implementation of Start-up:

In the below circuit net2 follows VDD. As net2 voltage rises greater than the threshold voltage with reference to net6 MP5 turns on there by allowing current through itself to net1. This regulates the net2 voltage and once device turns on net 6 remains at high voltage and there by isolating itself after turn on.



Part 9: Complete BGR circuit

After implementing all the blocks. The blocks are connected to get the complete BGR circuit.



BGR Circuit Design

1. Current Calculation

- Max. power Consumption < 60uW
- Max Total Current = $60 \text{ uW} / 1.8\text{V} = 33.33\text{uA}$ (1.8V VDD)
- So, we have chosen 10uA/branch, ($3 \times 10 = 30\text{uA}$)
- Start-up current 1-2 uA

2. Choosing Number of BJT in parallel in Branch2

- Less number of BJT: require less resistance value but matching hampers
- More number of BJT: requires higher resistance value but gives good matching
- So a moderate number have chosen (8 BJT) for better layout matching and moderate resistance value.

3. Calculation of R1

- $R1 = V_t \cdot \ln(8) / I = 26 \text{ mv} \cdot \ln(8) / 10.7\text{uA} = 5 \text{ KOhm}$
- R1 size: $W = 1.41\text{um}$, $L = 7.8\text{um}$, Unit res value: 2k Ohm
- Number of resistance needed: 2 in series and 2 in parallel ($2 + 2 + (2 \parallel 2)$)

4. Calculation of R2

- Current through ref branch: $I3 = I2 = V_t \cdot \ln(8) / R1$
- Voltage across R2: $R2 I3 = R2 / R1 (V_t \ln(8))$
- Slope of $V_{R2} = R2 / R1 (\ln(8) \cdot 115\text{uv}) / \text{Deg Cent.}$

- Slope of $V_{Q3} = -1.6\text{mV/Deg cent}$
- Adding both and equating to zero, R_2 will be around 33k Ohm
- Number of resistance needed: 16 in series and 2 in parallel ($2+2\ldots+2+ (2||2)$)

5. SBCM Design (Self-biased Current Mirror)

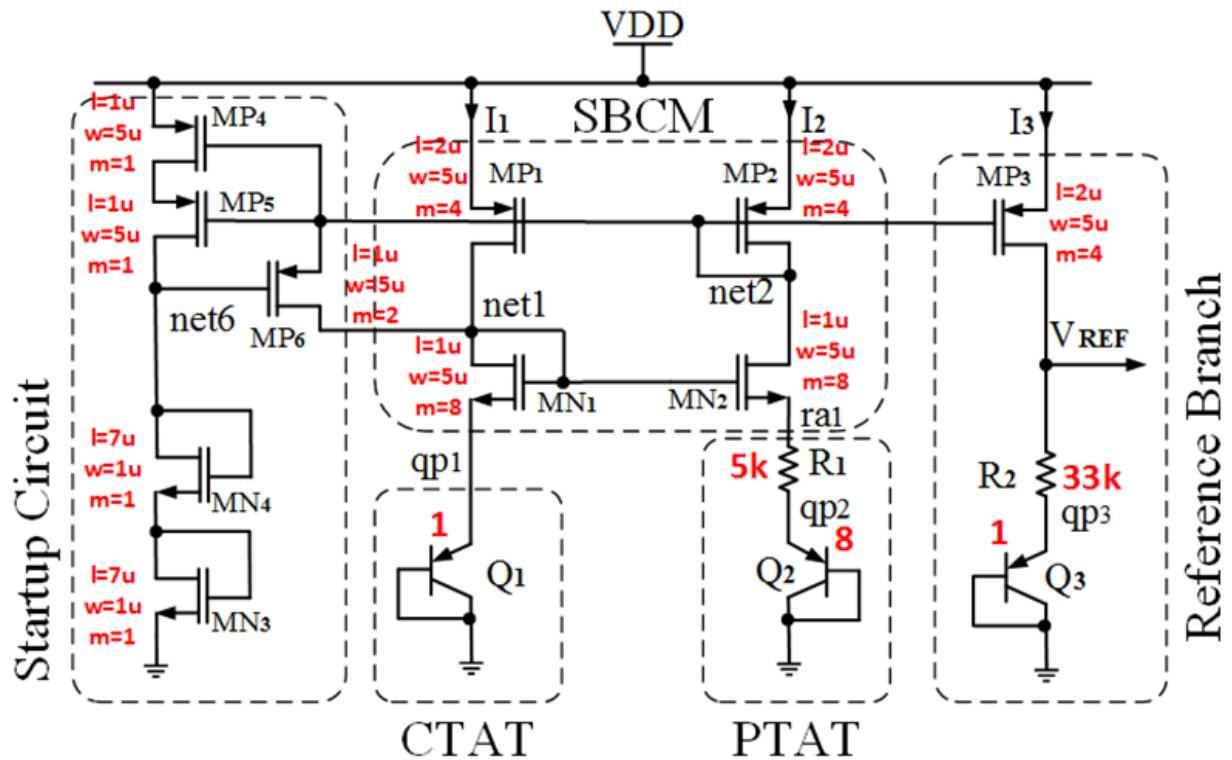
A. PMOS Design in SBCM

- Make both the MP1 and MP2 well in Saturation
- To reduce channel length modulation used $L=2\mu\text{m}$
- Finally the size is **$L=2\mu$, $W=5\mu$ and $M=4$**

B. NMOS Design in SBCM

- Make both the MN1 and MN2 either in Saturation or in deep sub-threshold
- We have made it in deep sub-threshold
- To reduce channel length modulation used $L=1\mu\text{m}$
- Finally the size is **$L=1\mu$, $W=5\mu$ and $M=8$**

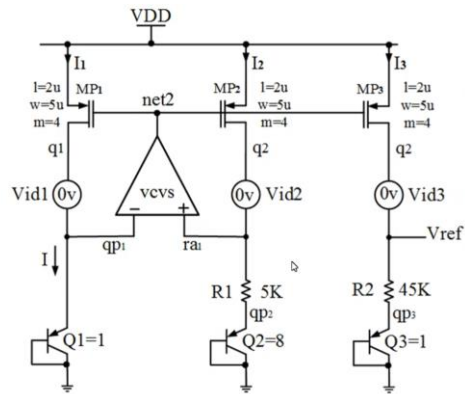
Final Circuit



Implementation:

BGR using Ideal OpAmp

After all blocks are done. BGR with VCVS or opamp is tested.



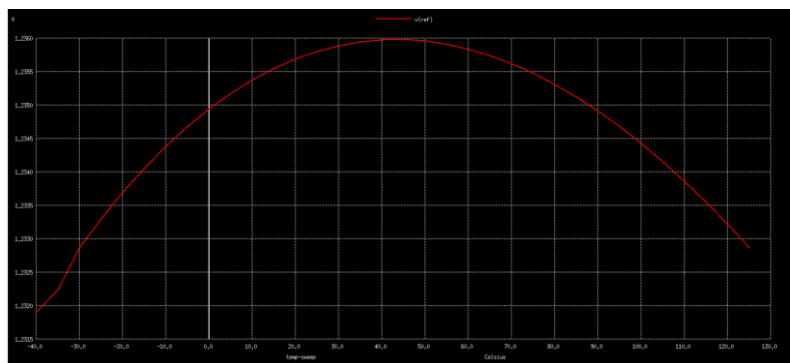
```
*** vcvs definition
e1 net2 gnd ral qp1 gain=1000
```

```
xmp1 qp1 net2 vdd vdd sky130_fd_pr_pfet_01v8_lvt l=2 w=5 m=4
xmp2 ral net2 vdd vdd sky130_fd_pr_pfet_01v8_lvt l=2 w=5 m=4
xmp3 ref net2 vdd vdd sky130_fd_pr_pfet_01v8_lvt l=2 w=5 m=4
```

```
*** bjt definition
xqp1 gnd gnd qp1 gnd sky130_fd_pr_pnp_05v5_W3p40L3p40 m=1
xqp2 gnd gnd qp2 gnd sky130_fd_pr_pnp_05v5_W3p40L3p40 m=8
xqp3 gnd gnd qp3 gnd sky130_fd_pr_pnp_05v5_W3p40L3p40 m=1
```

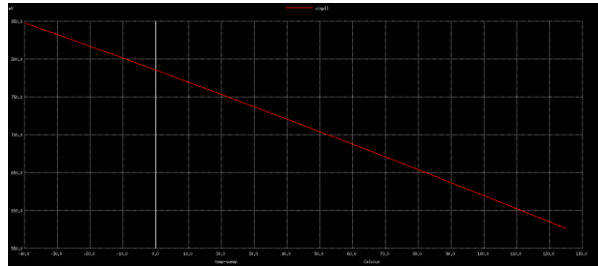
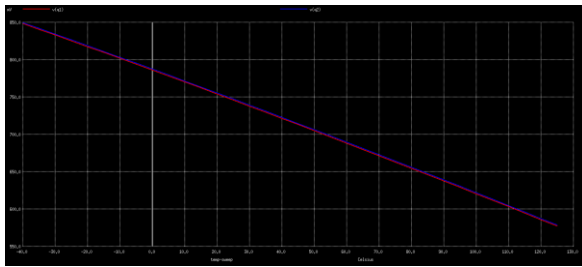
```
*** high-poly resistance definition
xra1 ral na1 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
xra2 na1 na2 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
xra3 na2 qp2 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
xra4 na2 qp2 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8

xrb1 ref nb1 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
xrb2 nb1 nb2 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
xrb3 nb2 nb3 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
xrb4 nb3 nb4 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
xrb5 nb4 nb5 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
xrb6 nb5 nb6 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
xrb7 nb6 nb7 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
xrb8 nb7 nb8 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
xrb9 nb8 nb9 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
xrb10 nb9 nb10 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
xrb11 nb10 nb11 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
xrb12 nb11 nb12 vdd sky130_fd_pr_res_high_po_1p41 w=1.41 l=7.8
```



In this simulation we should get the reference voltage as an umbrella shaped curve.

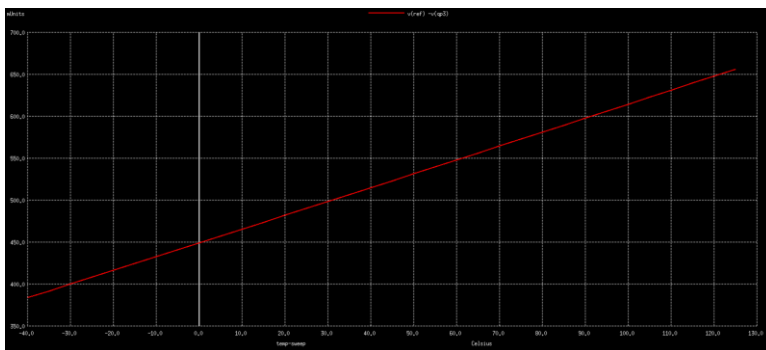
CTAT:



```
ngspice 1 -> plot vid1#branch vid2#branch
ngspice 1 -> plot v(qp3)
ngspice 1 ->
x0 = -35.4545, y0 = 0.74505

x0 = -19.8864, y0 = 0.815842    x1 = 82.2727, y1 = 0.649505
dx = 102.159, dy = -0.166337
dy/dx = -0.00162821    dx/dy = -614.171
```

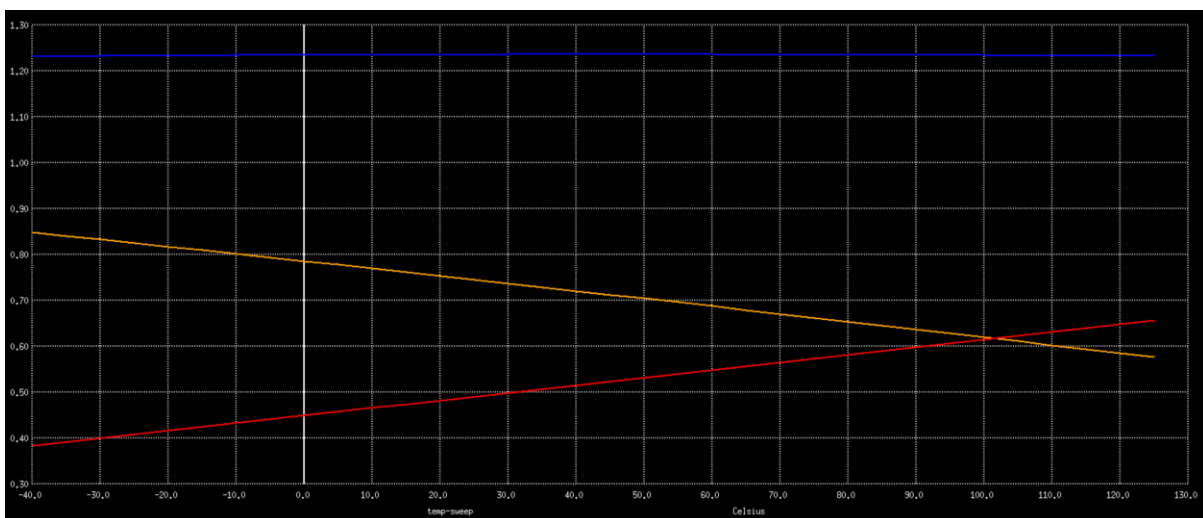
PTAT:



```
ngspice 1 -> plot v(ref) -v(qp3)
ngspice 1 ->
x0 = -32.6136, y0 = 0.523256

x0 = -0.113636, y0 = 0.448256    x1 = 90.5682, y1 = 0.6
dx = 90.6818, dy = 0.151744
dy/dx = 0.00167337    dx/dy = 597.597
```

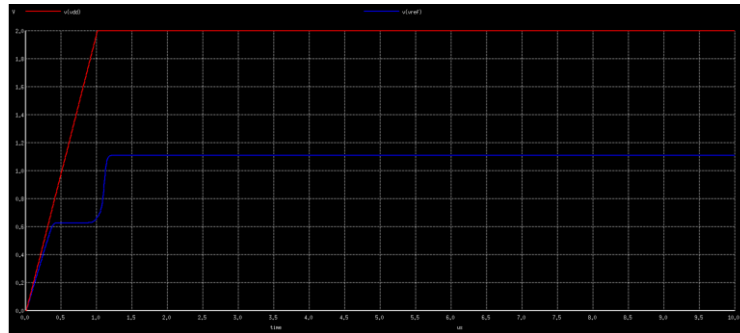
$$\text{CTAT} + \text{PTAT} = \text{VREF}$$



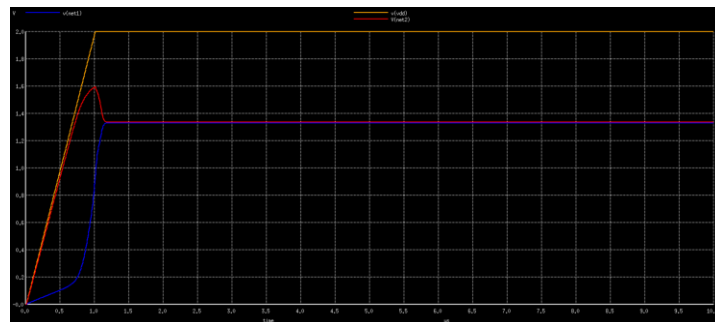
BGR with Start-up (SBCM)

With SBCM it is necessary to implement start-up circuit. Transient analysis is run to observe start-up behaviour of the circuit.

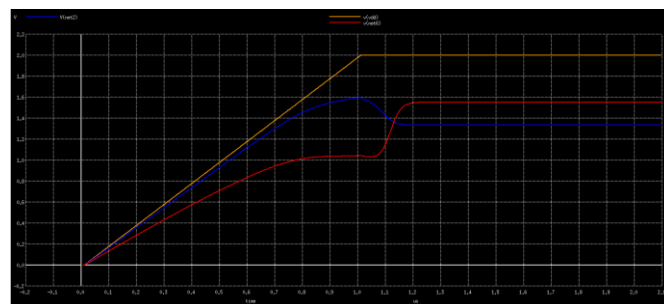
Vref raises as VDD increases and it can be observed start-up time is $\approx 1.25\mu\text{s}$ which is $< 2\mu\text{s}$ specification.



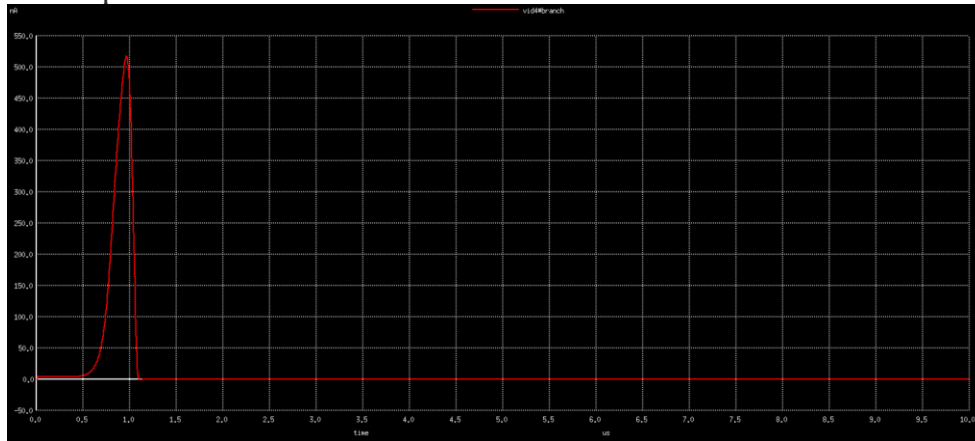
Voltage changes in net1 and net2, it can be observed during start up net2 follows vdd and after start up both settle at regulated value.



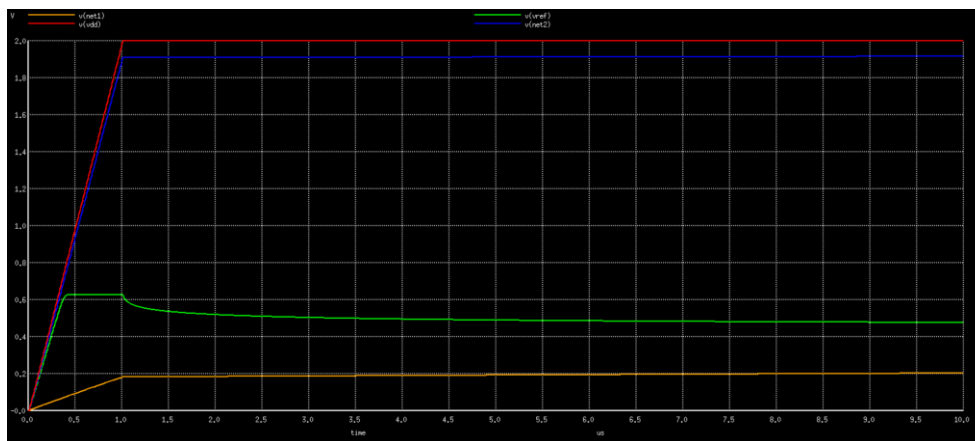
Below waveform shows how on net6 goes high and turns off startup circuit once device reaches desired operating point.



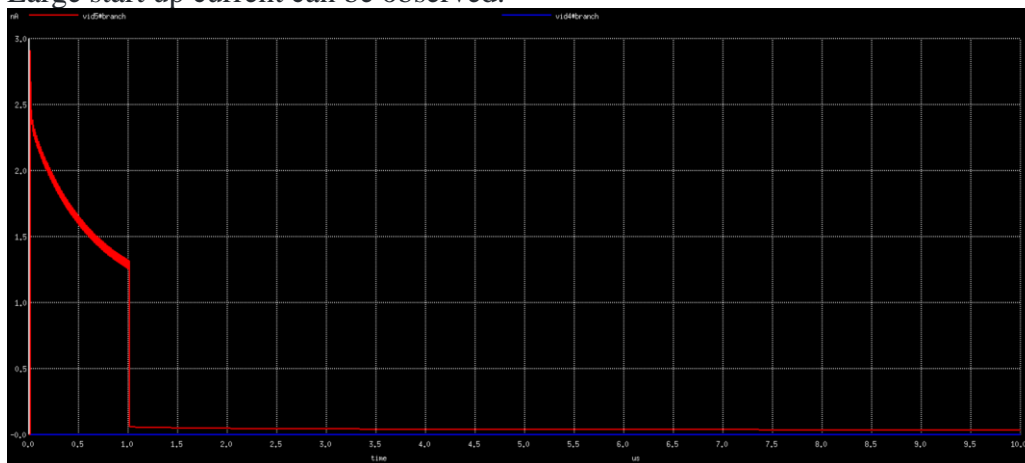
Start-up current waveform



To see effects of not using a start-up circuit, Start-up block was disabled in SBCM configuration.



It can be observed that net 1 doesn't go above 0.2V and Vref remains at a lower stable point. Large start up current can be observed.



Part 10: Layout of components

Now after getting our final netlist, we have to design the layout for our BGR. Layout is drawing the masks used in fabrication. We are going to use the Magic VLSI tool for our layout design.

Getting started with Magic

Magic is an open-source VLSI layout editor tool. To launch magic open terminal and write the following command.

```
$ magic -T /home/<path for sky130A.tech>/sky130A.tech
```

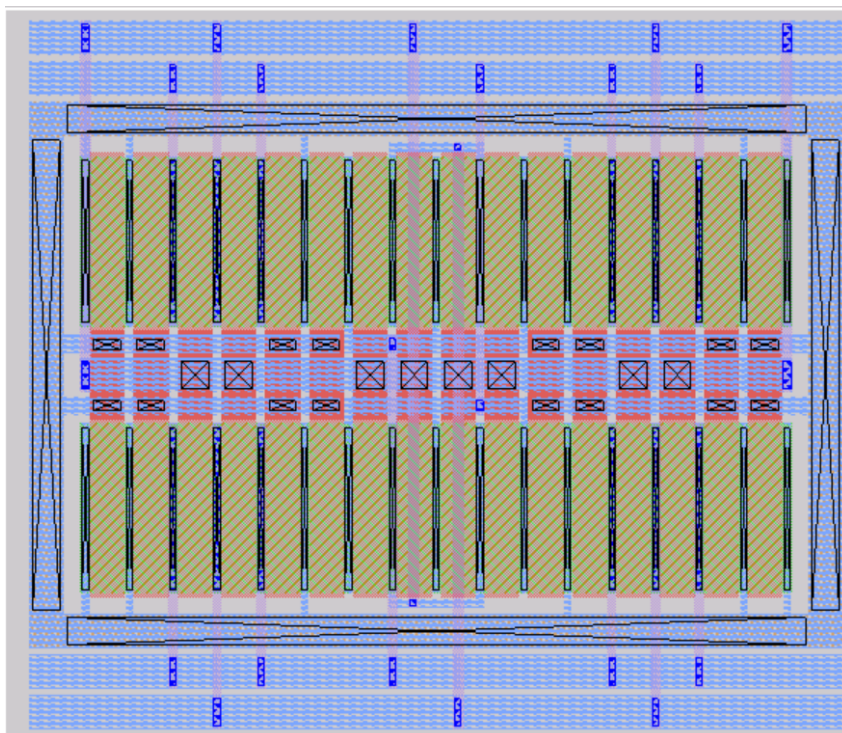
Now it will open up two windows, those are tkcon.tcl where we design and edit our Layout

Now device wise we have the following devices in our circuit.

- PFETS
- NFETS
- Resistor Bank
- BJTs

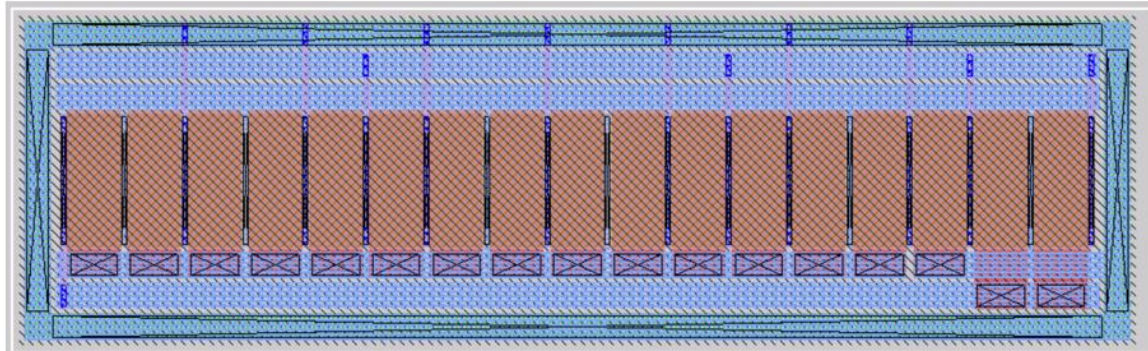
Design of NFET

In our circuit we are using LVT type NFETs. placed the nfets in such a way that it follows common centroid matching



Design of PFET

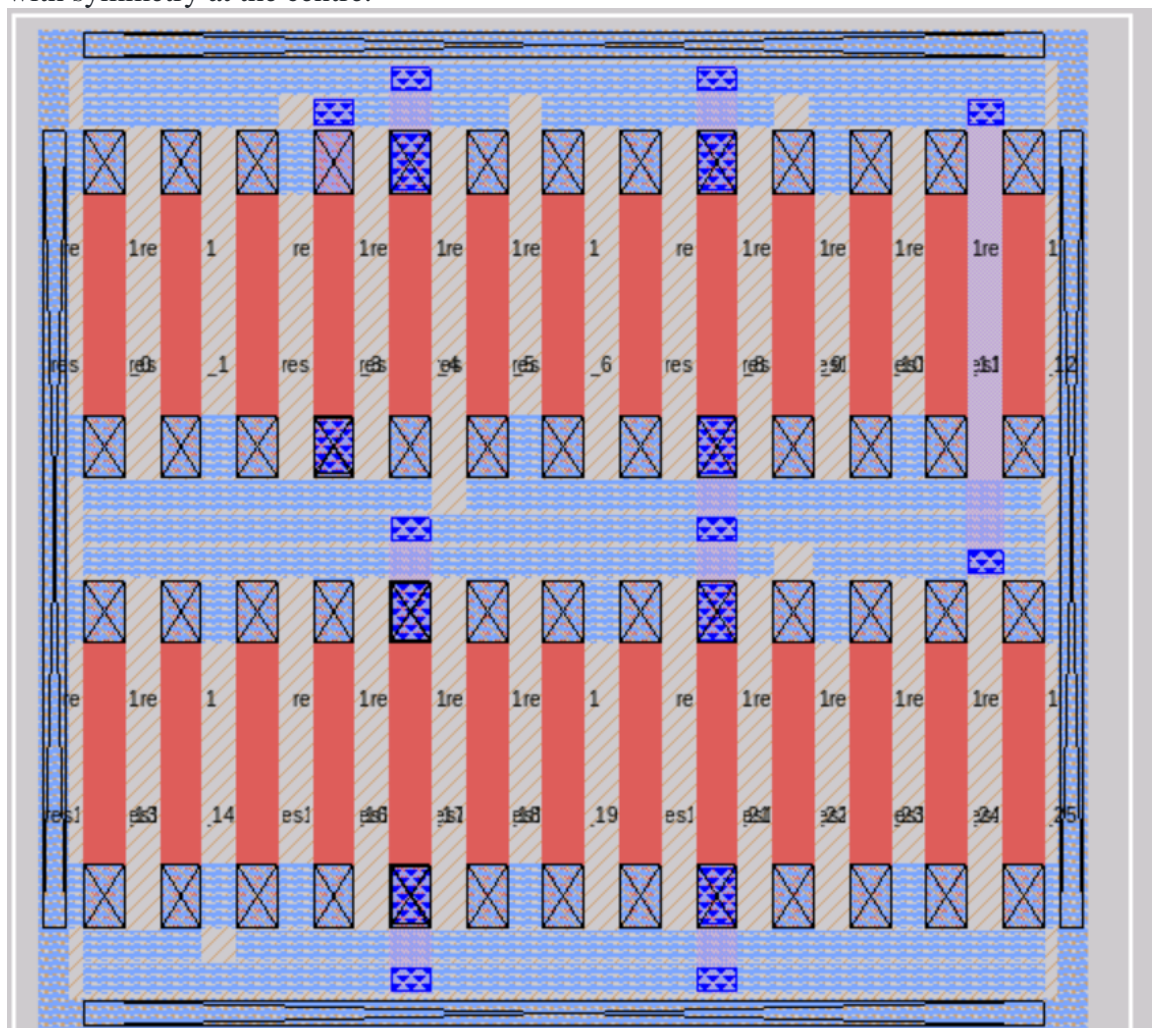
In our circuit we are using LVT type PFETs. These are matched from centre.



Design of Resistor

In our desing we are using poly resistors of $W=1.41$ and $L=7.8$.

9 poly resistors form R2 and 2 on corners form R1 and 2 dummy are placed. And matched with symmetry at the centre.



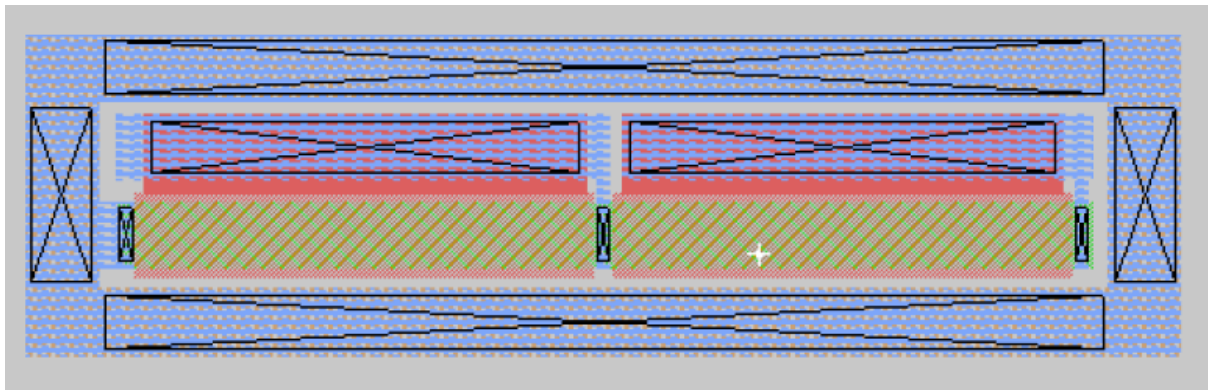
Design of PNP (BJT)

PNPT1_2 is Q1 and PNPT1_7 is Q3 at centre ,4 transistor on left and right are 8 Q2 rest are dummy.

pnpt1 pnpt1_27	pnpt1 pnpt1_15	pnpt1 pnpt1_16	pnpt1 pnpt1_17	pnpt1 pnpt1_18	pnpt1 pnpt1_19	pnpt1 pnpt1_20
pnpt1 pnpt1_26	pnpt1 pnpt1_0	pnpt1 pnpt1_1	pnpt1 pnpt1_2	pnpt1 pnpt1_3	pnpt1 pnpt1_4	pnpt1 pnpt1_21
pnpt1 pnpt1_25	pnpt1 pnpt1_5	pnpt1 pnpt1_6	pnpt1 pnpt1_7	pnpt1 pnpt1_8	pnpt1 pnpt1_9	pnpt1 pnpt1_22
pnpt1 pnpt1_24	pnpt1 pnpt1_10	pnpt1 pnpt1_11	pnpt1 pnpt1_12	pnpt1 pnpt1_13	pnpt1 pnpt1_14	pnpt1 pnpt1_23

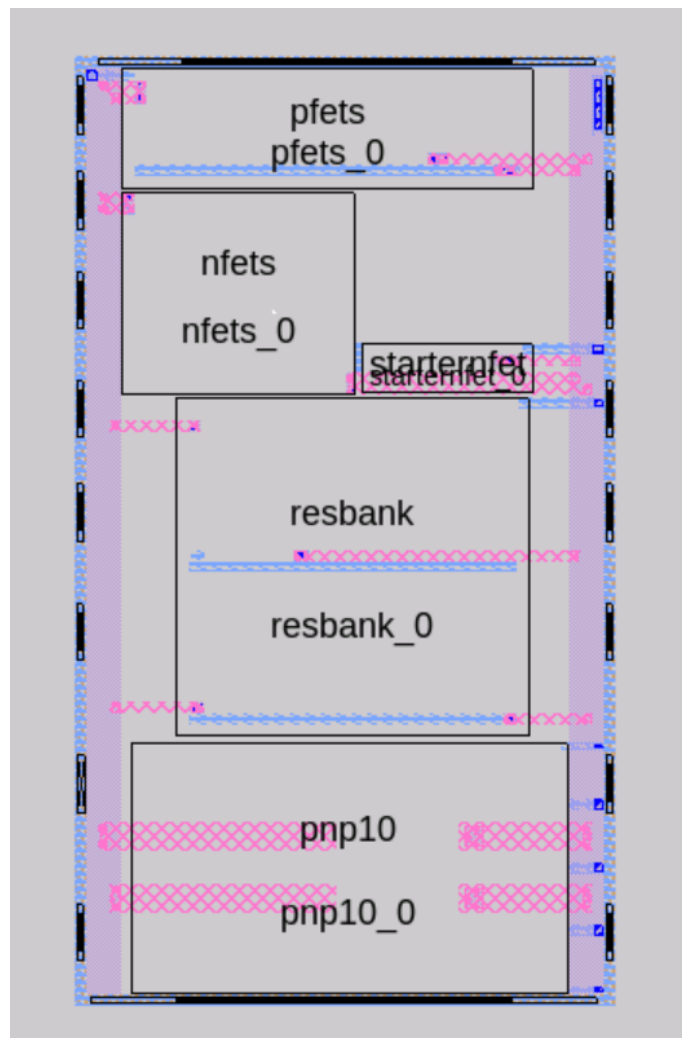
Design of STARTERNFET

We placed the the two w=1, l=7 NFETs



Top level design

To obtain the top level design, we have placed all the blocks together, routed it.

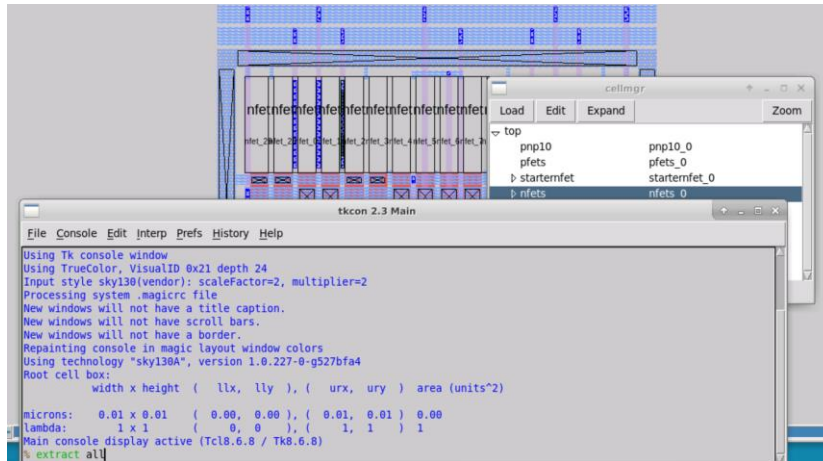


Part 11: Top level extraction and LVS

In order to do the parasitics extraction follow the steps given below:

- Open the Layout top.mag file >Options>Cell manger> select individual block and click open
- In the magic command window type extract, all. This extracts the layout connectivity information into a ".ext." file.
- Generally, if there are any warnings at this point, they would be because of wrong connections or short circuits or etc. But these are warnings and need not be errors.
- Now, we need to convert the ".ext" file to a ".spice" file to use for simulations.

- Use following commands:
 - Ext2sim label on
 - Ext2sim
 - Ext2spice scale off
 - Ext2spice hierarchy off
 - Ext2spice
- Run the above command for all the blocks and then finally on top level.



```
microns: 0.01 x 0.01 ( 0.00, 0.00 ), ( 0.01, 0.01 ) 0.00
lambda: 1 x 1 ( 0, 0 ), ( 1, 1 ) 1
Main console display active (Tcl8.6.8 / Tk8.6.8)
% extract all
Extracting nfet into nfet.ext:
Extracting nfets into nfets.ext:
% ext2sim label on
% ext2sim
exttosim finished.
% ext2spice scale off
% ext2spice hierarchy off
%
% ext2spice
exttosim finished.
%
```

```
* SPICE3 file created from nfets.ext - technology: sky130A

.subckt nfets net1 qpl gnd rpl net2
X0 rpl gnd gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X1 gnd gnd gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X2 gnd gnd qpl gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X3 gnd gnd rpl gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X4 qpl gnd gnd gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X5 rpl gnd gnd gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X6 net2 net1 rpl gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X7 net1 net1 qpl gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X8 rpl net1 net2 gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X9 qpl net1 net1 gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X10 gnd gnd qpl gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X11 net1 net1 qpl gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X12 gnd gnd gnd gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X13 qpl net1 net1 gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X14 gnd gnd rpl gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X15 gnd gnd gnd gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X16 gnd gnd rpl gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X17 qpl gnd gnd gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X18 qpl gnd gnd gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X19 gnd gnd gnd gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X20 net1 net1 qpl gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X21 qpl net1 net1 gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X22 net1 net1 qpl gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X23 qpl net1 net1 gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X24 gnd gnd qpl gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X25 rpl gnd gnd gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X26 net2 net1 rpl gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X27 rpl net1 net2 gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X28 net2 net1 rpl gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X29 rpl net1 net2 gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X30 net2 net1 rpl gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
X31 rpl net1 net2 gnd sky130 fd pr_nfet 0lv8 lvt ad=0p pd=0u as=0p ps=0u w=5e+06u l=1e+06u
C0 qpl net1 9.71FF
C1 rpl net2 7.43FF
C2 rpl net1 4.06FF
```

Observe the parasitic added.

LVS:

To run LVS open NETGEN and then type LVS “TOP.sp bgr” “TOP.spice top ”
/home/Abhijeet/cad_vds/eda-technology/sky130/tech/netgen/sky130_setup.tcl and run the LVS

```
Circuits match with 4 symmetries.  
Resolving automorphisms by property value.  
Resolving automorphisms by pin name.  
Netlists match with 2 symmetries.  
Circuits match correctly.  
Contents of circuit 1: Circuit: 'bgr'  
Circuit bgr contains 5 device instances.  
  Class: pfets           instances: 1  
  Class: nfets           instances: 1  
  Class: pnp10           instances: 1  
  Class: starternfet     instances: 1  
  Class: resbank         instances: 1  
Circuit contains 10 nets.  
Contents of circuit 2: Circuit: 'top'  
Circuit top contains 5 device instances.  
  Class: pfets           instances: 1  
  Class: nfets           instances: 1  
  Class: pnp10           instances: 1  
  Class: starternfet     instances: 1  
  Class: resbank         instances: 1  
Circuit contains 10 nets.  
  
Circuit 1 contains 5 devices, Circuit 2 contains 5 devices.  
Circuit 1 contains 10 nets, Circuit 2 contains 10 nets.  
  
Netlists match uniquely.  
Result: Circuits match uniquely.  
Logging to file "comp.out" disabled  
LVS Done.  
(work) 13 % |
```

And you should get netlist match uniquely.

Post layout Simulation:

In the top-level file include all the individually extracted spice file of all the block and then run ngspice simulation to obtain post layout result with effects of parasitic.

Conclusion and Opinion

The workshop is well paced program with good details on how to approach and start analog design. The hands-on experience is valuable in order to understand and retain the knowledge shared over two days. Step by step approach with connectivity between each module helps in learning concept from every angle. Would have preferred to have spent more time in understanding the calculation and analysis to determine the value of all the components such as resistors, BJT and FET's. Over all good experience and insight into availability of opensource tools to further learn more concepts

References

- <https://github.com/VrushabhDamle/sky130PLLdesignWorkshop>
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- <https://www.vsdia.com/>
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